NSN 5961-01-362-9720

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Inclosure Material:
Metal
Overall Length:
1.573 inches
Overall Height:
Between 0.250 inches and 0.450 inches
Overall Width:
1.050 inches
Function For Which Designed:
Rectifier
Mounting Facility Quantity:
2
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Cathode
Component Name And Quantity:
2 semiconductor device diode
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all semiconductor device diode
Voltage Rating In Volts Per Characteristic:
45.0 working peak reverse voltage all semiconductor device diode and 45.0 reverse voltage, instantaneous all semiconductor device diode
Current Rating Per Characteristic:
30.00 amperes forward current, average absolute all semiconductor device diode and 500.00 amperes forward current, average preset all
semiconductor device diode
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Special Features:
All semiconductor device diode junction pattern arrangement: pn
Special Test Features:
Selected and tested for the milstar Irip program
Test Data Document:
49956-g309036 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
2 pin and 1 case
Shelf Life:
N/a

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Unit Of Measure:

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Demilitarization:

No

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